

N-Channel 80 V (D-S) MOSFET

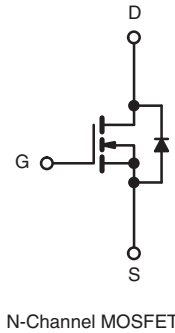
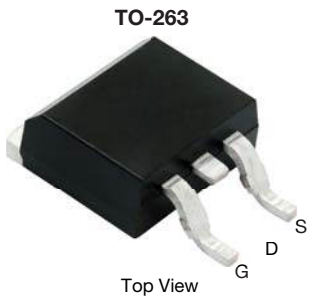
PRODUCT SUMMARY		
V_{DS}	80	V
$R_{DS(on)}$ $V_{GS} = 10\text{ V}$	6	$m\Omega$
$R_{DS(on)}$ $V_{GS} = 4.5\text{ V}$	10	$m\Omega$
I_D	120	A
Configuration	Single	

FEATURES

- ThunderFET® power MOSFET
- Maximum 175 °C junction temperature
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see



RoHS
COMPLIANT



ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ °C}$, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	80	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150\text{ °C}$)	I_D	$T_C = 25\text{ °C}$	120
		$T_C = 125\text{ °C}$	65
Pulsed Drain Current ($t = 100\ \mu\text{s}$)	I_{DM}	225	A
Avalanche Current	I_{AS}	L = 0.1 mH	50
Single Avalanche Energy ^a			E_{AS}
Maximum Power Dissipation ^a	P_D	$T_C = 25\text{ °C}$	370 ^b
		$T_C = 125\text{ °C}$	120 ^b
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	0.75	

Notes

- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

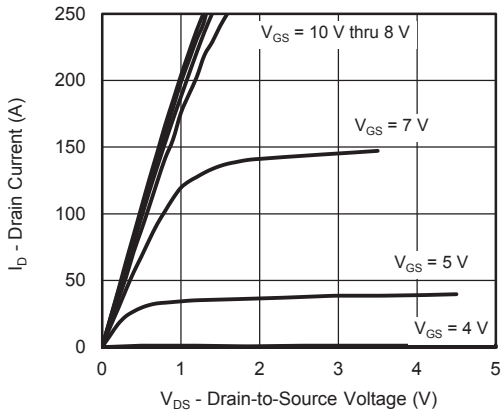
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	80	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5	-	4.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V	-	-	1	μA
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 175 °C	-	-	2	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 10 V, V _{GS} = 10 V	90	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	6	-	mΩ
		V _{GS} = 4.5V, I _D = 30 A	-	10	-	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	-	85	-	S
Dynamic ^b						
Input Capacitance	C _{ISS}	V _{GS} = 0 V, V _{DS} = 40 V, f = 1 MHz	-	3330	-	pF
Output Capacitance	C _{OSS}		-	1395	-	
Reverse Transfer Capacitance	C _{rss}		-	95	-	
Total Gate Charge ^c	Q _g	V _{DS} = 40 V, V _{GS} = 10 V, I _D = 30 A	-	53.5	81	nC
Gate-Source Charge ^c	Q _{gs}		-	14.5	-	
Gate-Drain Charge ^c	Q _{gd}		-	13.2	-	
Gate Resistance	R _g	f = 1 MHz	0.9	1.9	3.8	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 40 V, R _L = 1.67 Ω I _D ≅ 30 A, V _{GEN} = 10 V, R _g = 1 Ω	-	13	26	ns
Rise Time ^c	t _r		-	22	44	
Turn-Off Delay Time ^c	t _{d(off)}		-	27	54	
Fall Time ^c	t _f		-	9	18	
Drain-Source Body Diode Ratings and Characteristics ^b (T_C = 25 °C)						
Pulsed Current (t = 100 μs)	I _{SM}		-	-	240	A
Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V	-	0.86	1.4	V
Reverse Recovery Time	t _{rr}	I _F = 30 A, di/dt = 100 A/μs	-	88	176	ns
Peak Reverse Recovery Charge	I _{RM(REC)}		-	5	10	A
Reverse Recovery Charge	Q _{rr}		-	0.22	0.44	μC

Notes

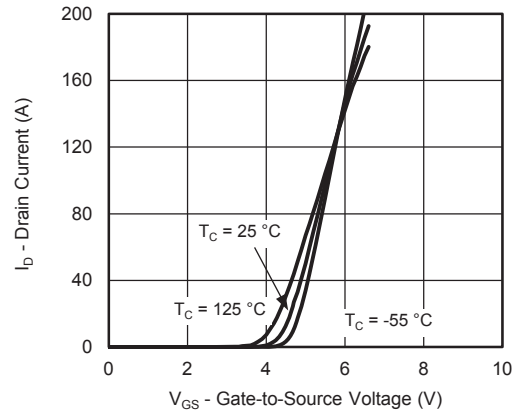
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

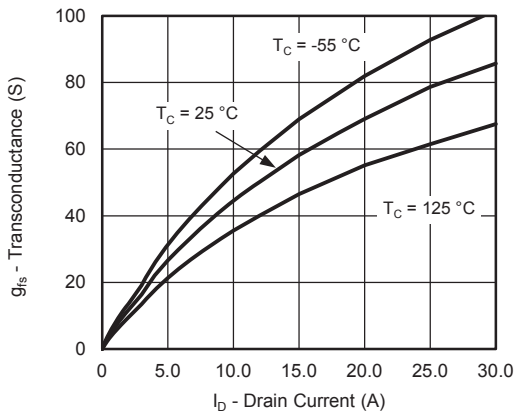
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



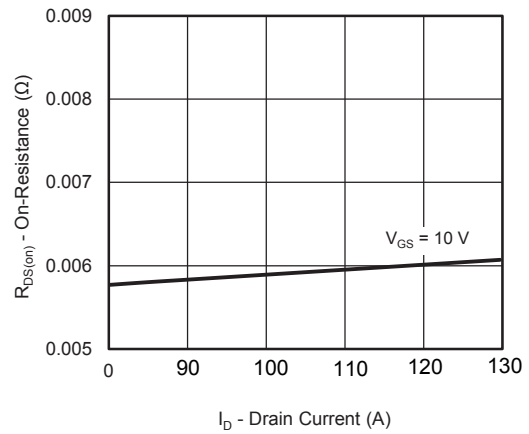
Output Characteristics



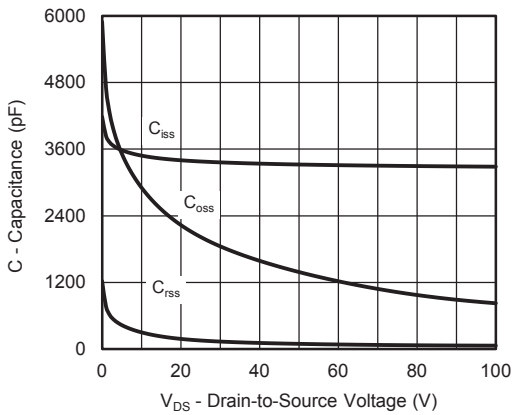
Transfer Characteristics



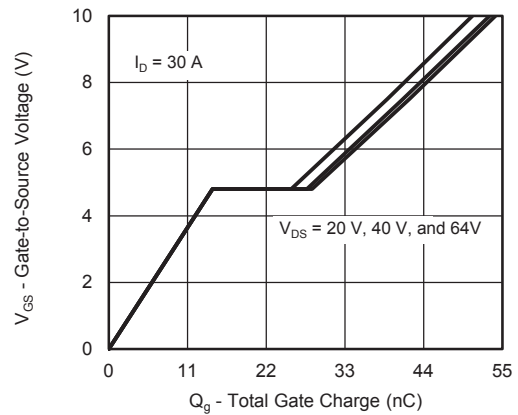
Transconductance



On-Resistance vs. Drain Current

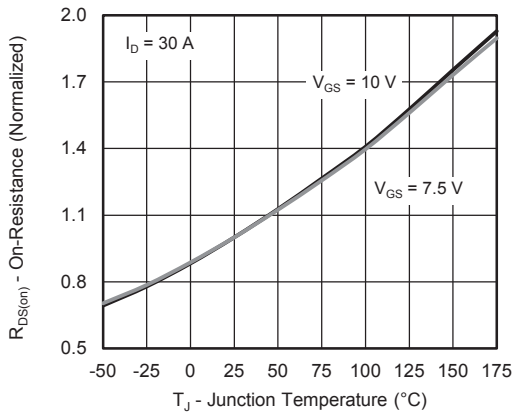


Capacitance

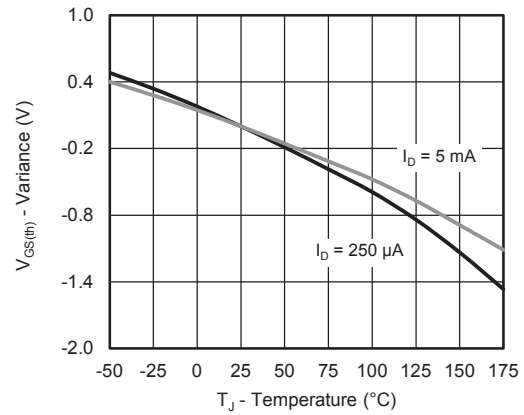


Gate Charge

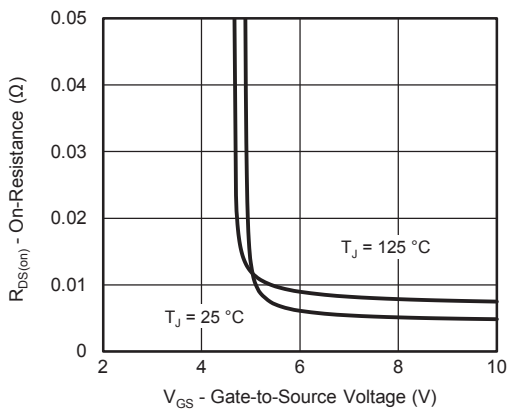
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



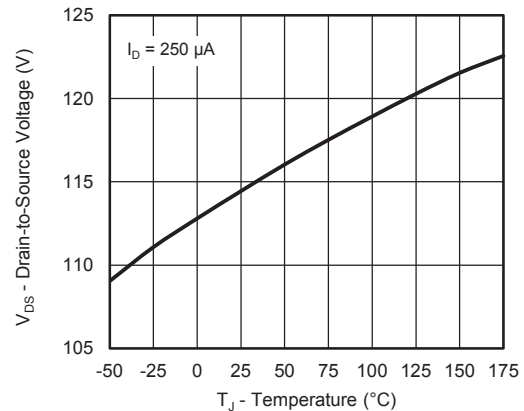
On-Resistance vs. Junction Temperature



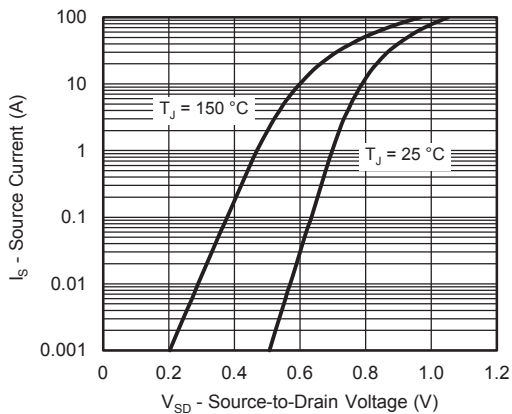
Threshold Voltage



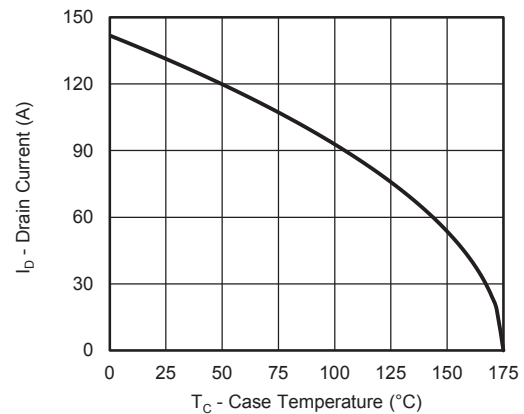
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

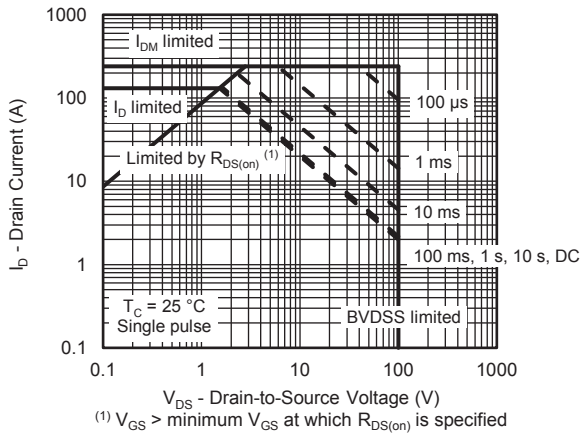


Source Drain Diode Forward Voltage



Current De-Rating

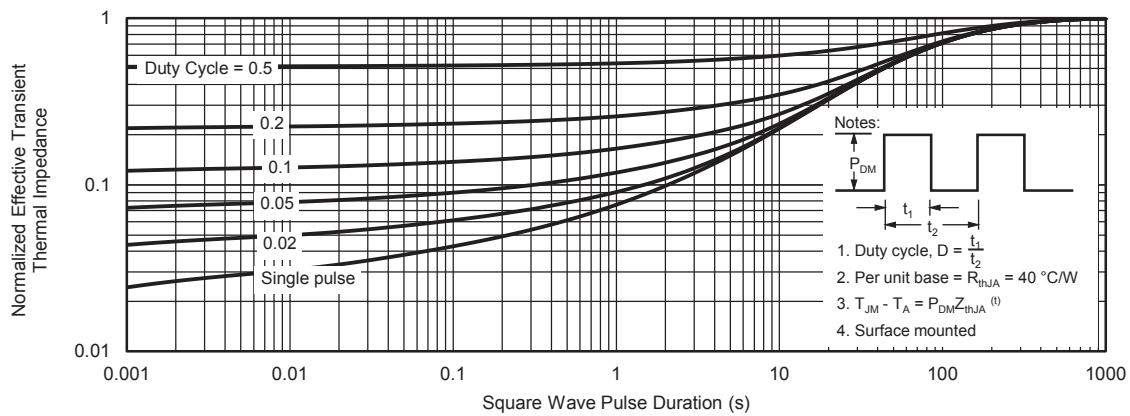
THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Safe Operating Area



I_{DAV} vs. Time



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

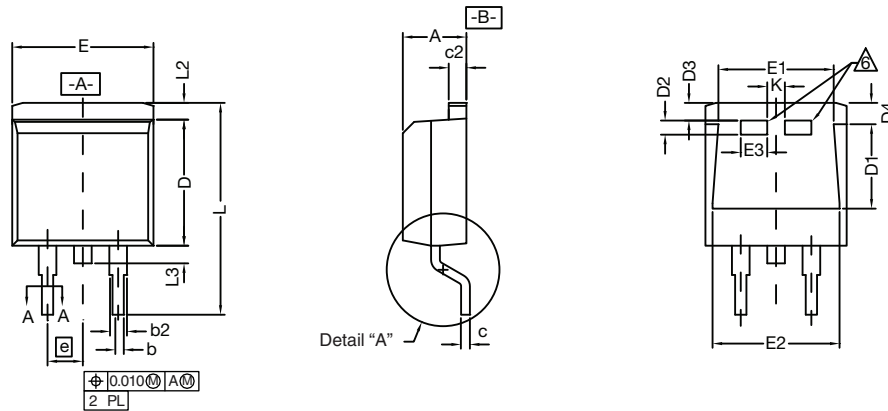


Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^\circ\text{C}$)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

TO-263 (D²PAK): 3-LEAD



DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
$\textcircled{E3}$	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- $\textcircled{6}$: This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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